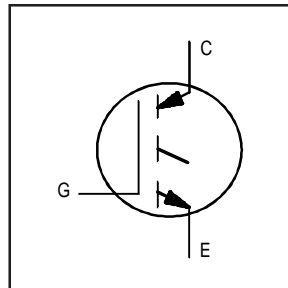


IRG4CH50UB

IRG4CH50UB IGBT Die in Wafer Form



1200 V
 Size 5
 Ultra-Fast Speed
 6" Wafer

Electrical Characteristics (Wafer Form)

Parameter	Description	Guaranteed (Min/Max)	Test Conditions
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	4.5V Max.	$I_C = 10A, T_J = 25^\circ C, V_{GE} = 15V$
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200V Min.	$T_J = 25^\circ C, I_{CES} = 250\mu A, V_{GE} = 0V$
$V_{GE(th)}$	Gate Threshold Voltage	3.0V Min., 6.0V Max.	$V_{GE} = V_{CE}, T_J = 25^\circ C, I_C = 250\mu A$
I_{CES}	Zero Gate Voltage Collector Current	300 μA Max.	$T_J = 25^\circ C, V_{CE} = 1200V$
I_{GES}	Gate-to-Emitter Leakage Current	$\pm 11 \mu A$ Max.	$T_J = 25^\circ C, V_{GE} = +/- 20V$

Mechanical Data

Norminal Backmetal Composition, Thickness:	Cr-Ni / V-Ag (1kA-2kA-.2.5kA)
Norminal Front Metal Composition, Thickness:	99% Al, 1% Si (4 microns)
Dimensions:	0.257" x 0.260"
Wafer Diameter:	150mm, with std. < 100 > flat
Wafer thickness:	.015" + / -.003"
Relevant Die Mechanical Dwg. Number	01-5227
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Ink Dot Location	Consistent throughout same wafer lot
Recommended Storage Environment:	Store in original container, in dessicated nitrogen, with no contamination

Reference Standard IR packaged part (for design) : IRG4PH50U

Die Outline

